

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

HN2S01FU

LOW VOLTAGE HIGH SPEED SWITCHING APPLICATION

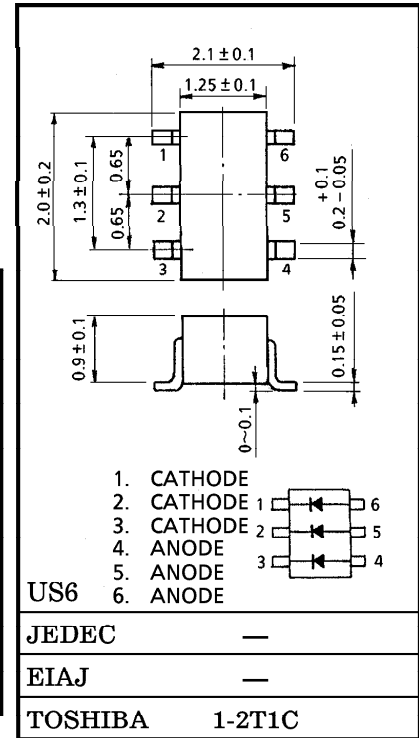
Unit in mm

- HN2S01F is composed of 3 independent diodes.
- Low Forward Voltage : $V_F = 0.23V$ (TYP.) @ $I_F = 5mA$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Maximum (Peak) Forward Current	I_{FM}	200*	mA
Average Forward Current	I_O	100*	mA
Surge Current (10ms)	I_{FSM}	1*	A
Power Dissipation	P	200	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55~125	°C
Operating Temperature Range	T_{opr}	-40~100	°C

* : This is the Maximum Ratings of single diode (Q1 or Q2 or Q3).
 In the case of using 2 or 3 diodes, the Maximum Ratings per diode is 75% of the single diode one.

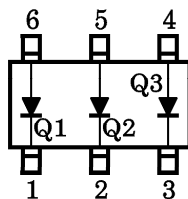


Weight : 6.2mg

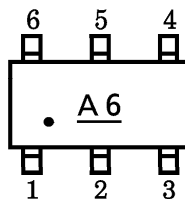
ELECTRICAL CHARACTERISTICS (Q1, Q2, Q3 COMMON Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F (1)	$I_F = 1mA$	—	0.18	—	V
	V_F (2)	$I_F = 5mA$	—	0.23	0.30	
	V_F (3)	$I_F = 100mA$	—	0.35	0.50	
Reverse Current	I_R	$V_R = 10V$	—	—	20	μA
Total Capacitance	C_T	$V_R = 0, f = 1MHz$	—	20	40	pF

PIN ASSIGNMENT (TOP VIEW)



MARKING

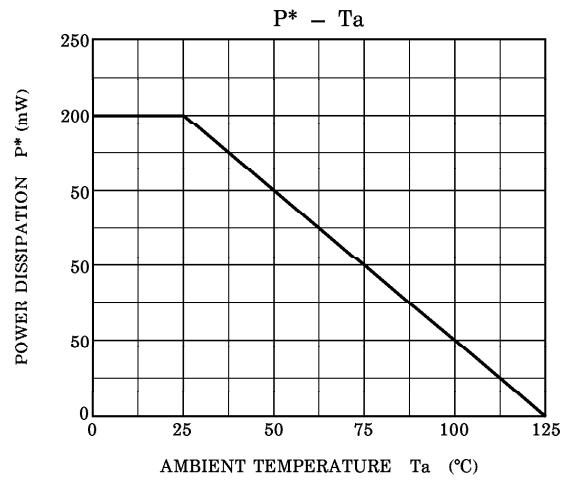
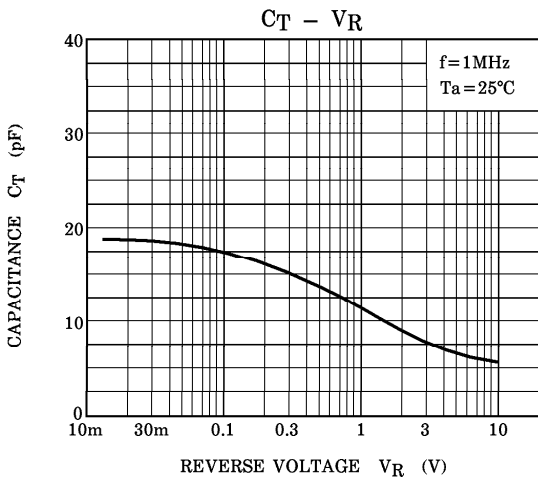
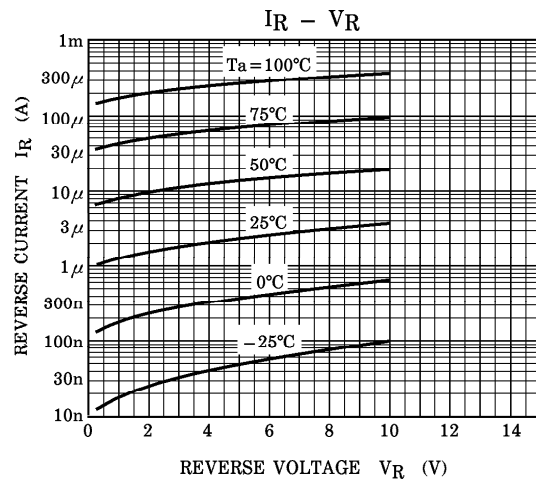
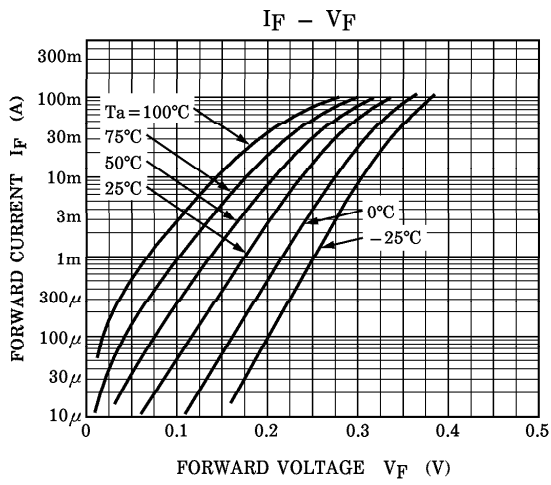


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* : Total Rating